



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = +25^\circ C$
-20V	600m Ω @ $V_{GS} = -4.5V$	-0.92A
	900m Ω @ $V_{GS} = -2.7V$	-0.75A

Features and Benefits

- Fast switching speed
- Low on-resistance
- Low threshold
- Low gate drive

Description and Applications

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed, making it ideal for high-efficiency power management applications.

- DC - DC converters
- Power management functions
- Disconnect switches
- Motor control

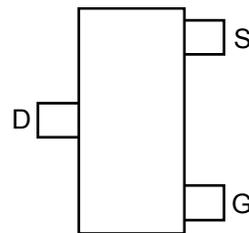
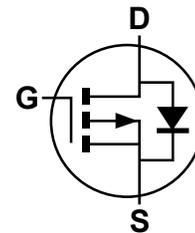
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)

SOT23



Top View


 Top View
Pin Out


Equivalent Circuit

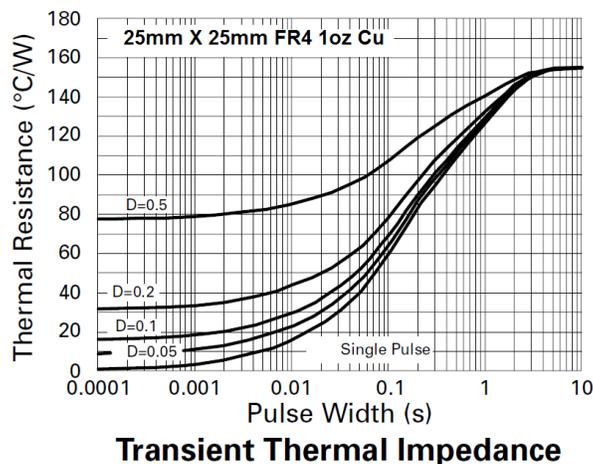
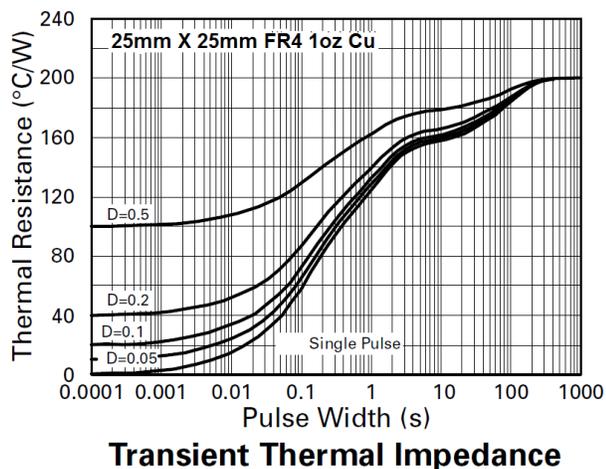
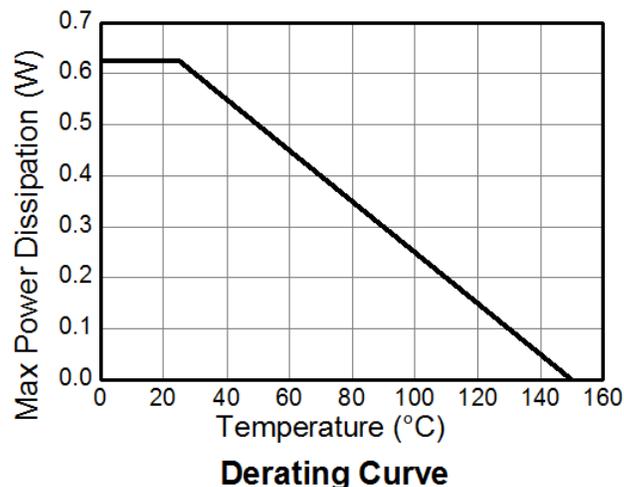
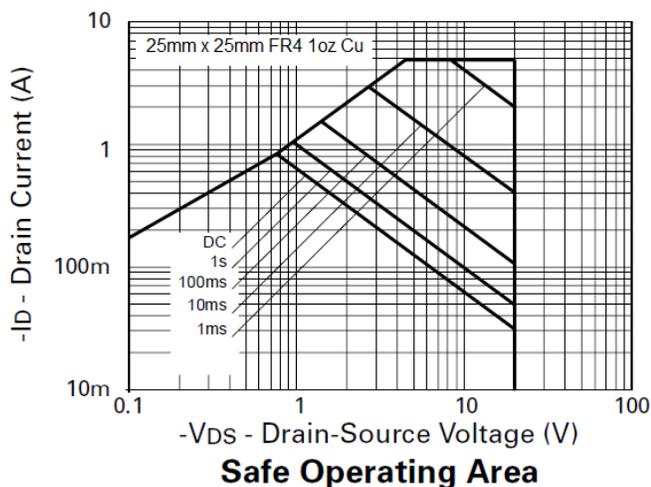
Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GS}	± 12	V
Continuous Drain Current	$V_{GS} = 4.5\text{V}$	$T_A = +25^\circ\text{C}$ (Note 6)	I_D	-0.9	A
		$T_A = +70^\circ\text{C}$ (Note 6)	I_D	-0.7	A
Pulsed Drain Current (Note 7)			I_{DM}	-4.9	A
Continuous Source Current (Body Diode) (Note 6)			I_S	-0.9	A
Pulsed Source Current (Body Diode) (Note 7)			I_{SM}	-4.9	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	625	mW
Linear Derating Factor		5	mW/ $^\circ\text{C}$
Power Dissipation (Note 6)	P_D	806	mW
Linear Derating Factor		6.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	155	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
 6. For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.
 7. Repetitive rating 25mm x 25mm FR4 PCB, $D=0.05$ pulse width=10 μs - pulse current limited by maximum junction temperature.

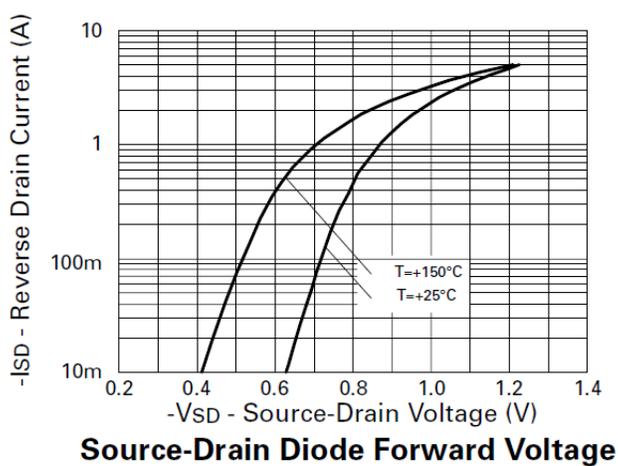
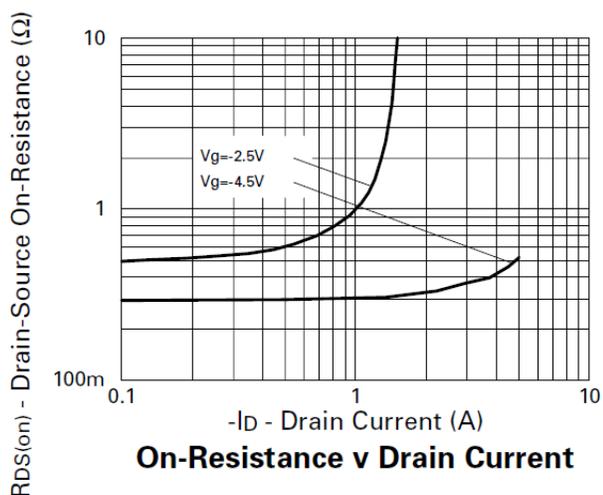
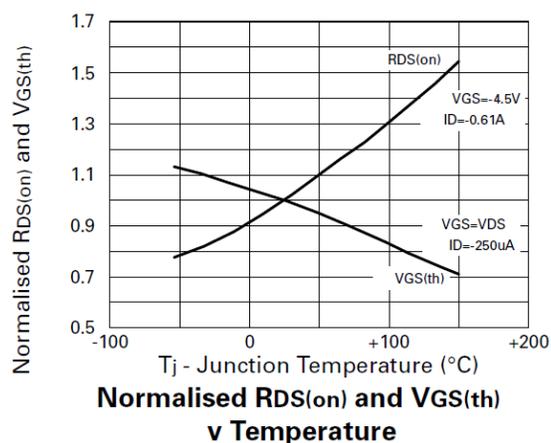
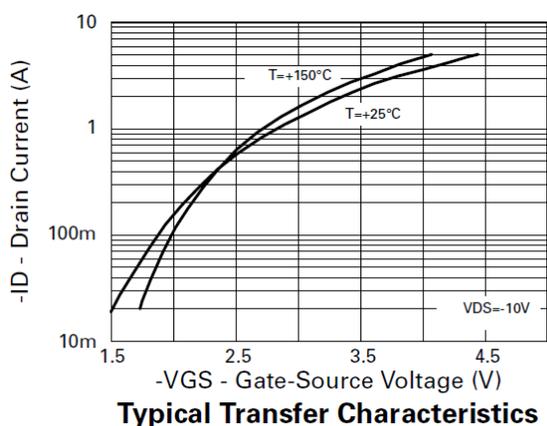
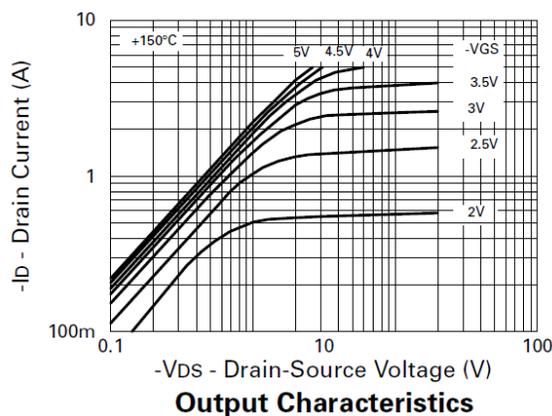
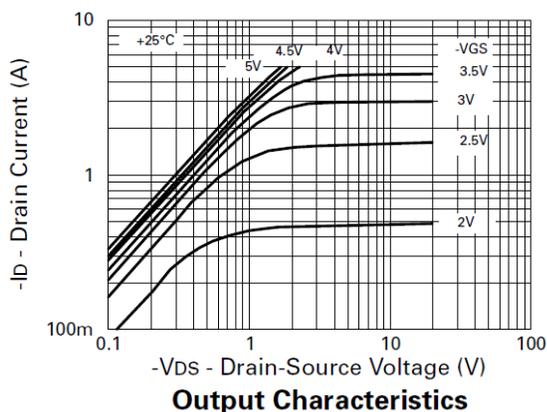
Thermal Characteristics


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

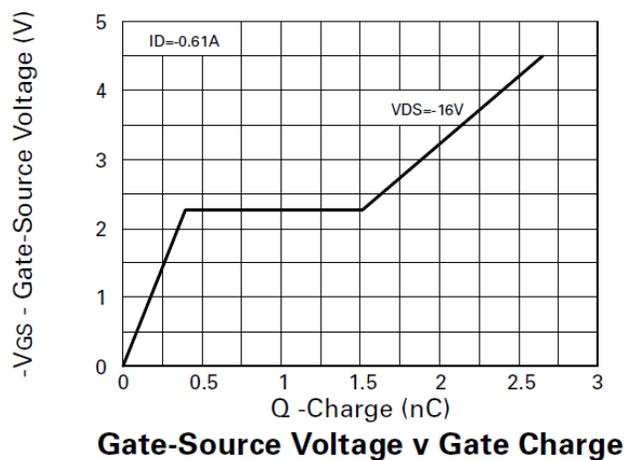
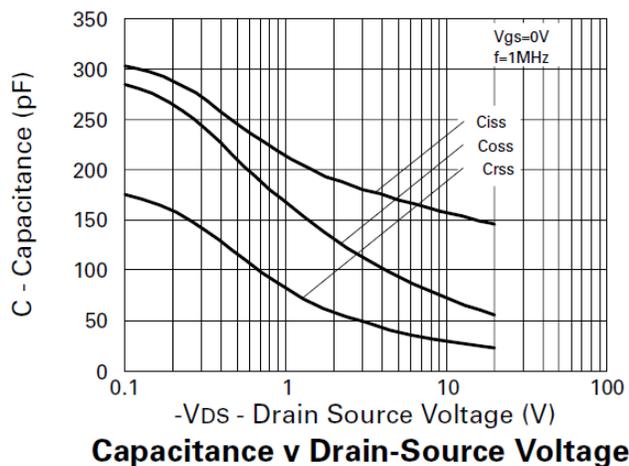
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	I _D = -250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-0.1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	-0.7	—	-1.5	V	I _D = -250μA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance (Note 8)	R _{DS(ON)}	—	—	0.6 0.9	Ω	V _{GS} = -4.5V, I _D = -0.61A V _{GS} = -2.7V, I _D = -0.31A
Forward Transconductance (Notes 8 and 10)	g _{fs}	0.56	—	—	S	V _{DS} = -10V, I _D = -0.31A
Diode Forward Voltage (Note 8)	V _{SD}	—	—	-0.95	V	T _J = +25°C, I _S = -0.61A, V _{GS} = 0V
Reverse Recovery Time (Note 10)	t _{rr}	—	14.9	—	ns	T _J = +25°C, I _F = -0.61A,
Reverse Recovery Charge (Note 10)	Q _{rr}	—	5.6	—	nC	di/dt = 100A/μs
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	150	—	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	70	—		
Reverse Transfer Capacitance	C _{rss}	—	30	—		
Turn-On Delay Time (Note 9)	t _{d(on)}	—	2.9	—	ns	V _{DD} = -110V, I _D = -0.93A, R _G ≅ 6.2Ω, R _D ≅ 11Ω,
Turn-On Rise Time (Note 9)	t _r	—	6.7	—		
Turn-Off Delay Time (Note 9)	t _{d(off)}	—	11.2	—		
Turn-Off Fall Time (Note 9)	t _f	—	10.1	—		
Total Gate Charge (Note 9)	Q _g	—	3.5	—	nC	V _{DS} = -16V, V _{GS} = -4.5V, I _D = -0.61A
Gate-Source Charge (Note 9)	Q _{gs}	—	0.5	—		
Gate-Drain Charge (Note 9)	Q _{gd}	—	1.5	—		

- Notes:
8. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤ 2%.
 9. Switching characteristics are independent of operating junction temperature.
 10. For design aid only, not subject to production testing.

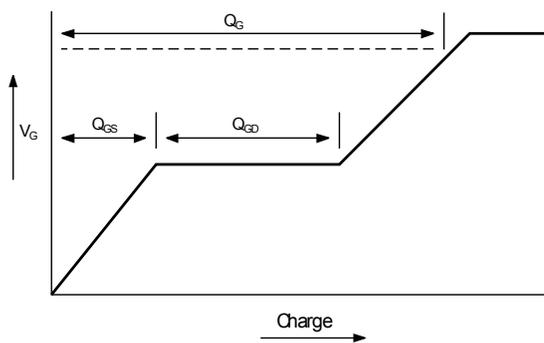
Typical Characteristics



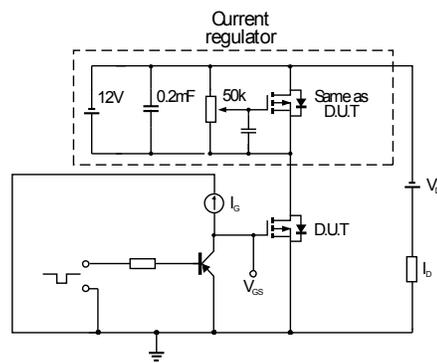
Typical Characteristics - continued



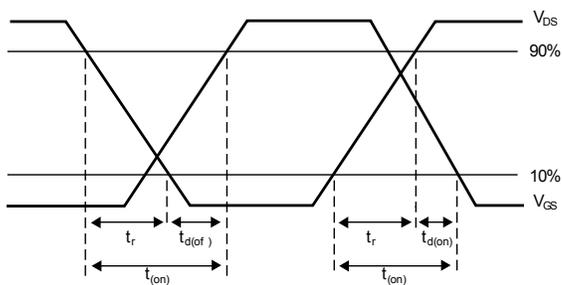
Test Circuits



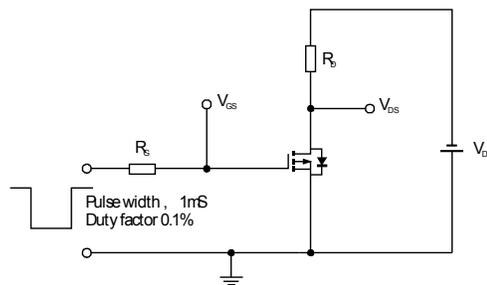
Basic gate charge waveform



Gate charge test circuit

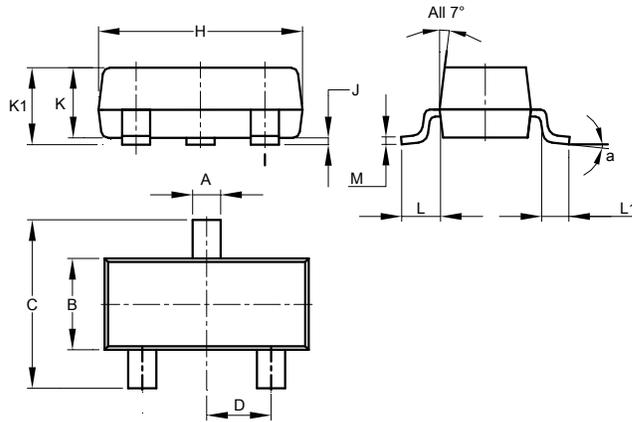


Switching time waveforms



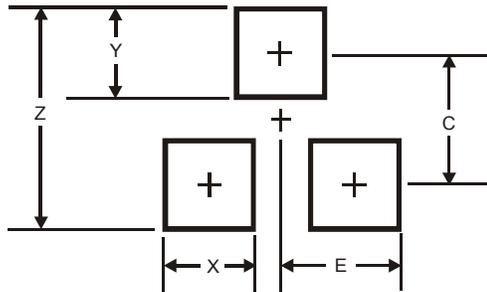
Switching time test circuit

Package Outline Dimensions



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35